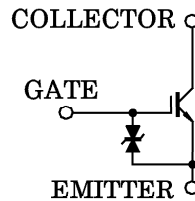


TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

GT8G103

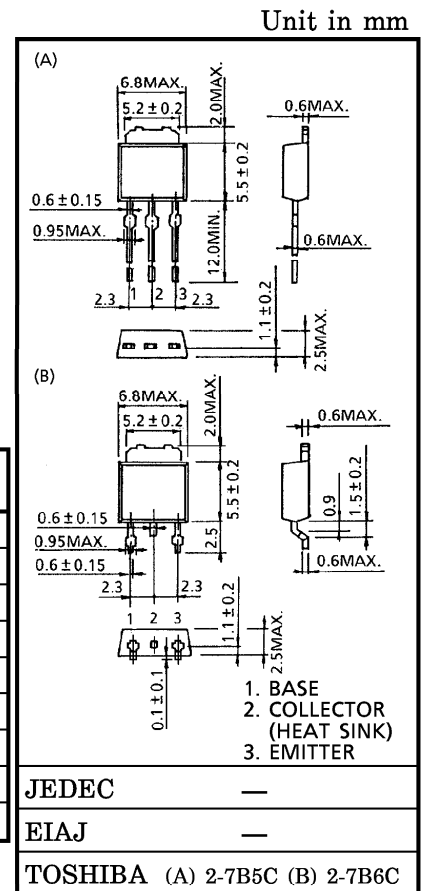
STROBE FLASH APPLICATIONS

- 3rd Generation
- Enhancement-Mode
- Low Saturation Voltage
: $V_{CE(sat)} = 8\text{ V (Max.)}$ ($@I_C = 150\text{ A}$)
- 4.5 V Gate Drive



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	400	V
Gate-Emitter Voltage	DC	V_{GES}	± 6 V
	Pulse	V_{GES}	± 8 V
Collector Current	DC	I_C	8 A
	1 ms	I_{CP}	150 A
Collector Power	$T_a = 25^\circ\text{C}$	P_C	1.3 W
Dissipation	$T_c = 25^\circ\text{C}$	P_C	20 W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.36 g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE} = 6\text{ V}, V_{CE} = 0$	—	—	10	μA
Collector Cut-off Current	I_{CES}	$V_{CE} = 400\text{ V}, V_{GE} = 0$	—	—	10	μA
Gate-Emitter Cut-off Voltage	$V_{GE(OFF)}$	$I_C = 1\text{ mA}, V_{CE} = 5\text{ V}$	0.5	—	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{ A}, V_{GE} = 4.5\text{ V (Pulsed)}$	—	5	8	V
Input Capacitance	C_{ies}	$V_{CE} = 10\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	—	1900	—	pF
Switching Time	Rise Time	 $V_{IN} : t_r \leq 100\text{ ns}$ $t_f \leq 100\text{ ns}$ Duty cycle $\leq 1\%$	—	1.2	—	μs
	Turn-on Time		—	1.4	—	
	Fall Time		—	1.8	—	
	Turn-off Time		—	2.4	—	
Thermal Resistance	$R_{th(j-c)}$	—	—	—	6.25	°C/W

These devices are MOS type. Users should follow proper ESD Handling Procedures.

Operating condition of turn-off dv/dt should be lower than $400\text{ V}/\mu\text{s}$.

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